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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0018			
I <sub>D</sub> (A)	200			
Configuration	Single			
Package	TO-263-7L			

#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R<sub>q</sub> and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

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Top View G	N-Channel I	G O O O O O O O O O O O O O O O O O O O
<b>DLUTE MAXIMUM RATINGS</b> ( $T_C = 25  ^{\circ}C$ , unles	s otherwise noted)	
METER	SYMBOL	LIMIT

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	Drain-Source Voltage		40	V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	- I <sub>D</sub>	200		
Continuous Drain Current	T <sub>C</sub> = 125 °C		192		
Continuous Source Current (Diode Conduction	I <sub>S</sub>	200	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	600			
Single Pulse Avalanche Current	L = 0.1 mH	l <sub>AS</sub>	85		
Single Pulse Avalanche Energy	L = 0.1 11111	E <sub>AS</sub>	361	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Б	375	W	
Maximum Fower Dissipation -	T <sub>C</sub> = 125 °C	$P_{D}$	125	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	40	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	0.4	C/VV	

#### **Notes**

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$ .
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1	1		L			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	200	-	-	Α
	. ,	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0015	0.0018	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0028	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0034	
Forward Transconductance b	9 <sub>fs</sub>	$V_{DS}$	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		198	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	13 880	17 350	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		1414	1770	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	840	1050	
Total Gate Charge <sup>c</sup>	$Q_g$			-	206	310	
Gate-Source Charge c	$Q_{gs}$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 120 \text{ A}$	-	50	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	44	-	
Gate Resistance	$R_g$		f = 1 MHz		0.8	1.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	26	39	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 0.17 $\Omega$ $I_D$ $\cong$ 120 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	21	32	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	68	102	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18	
Source-Drain Diode Ratings and Characteristics b							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	600	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V			0.86	1.5	V

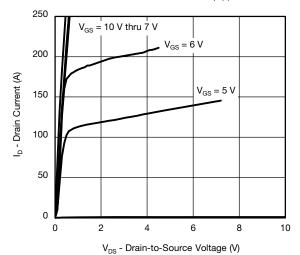
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

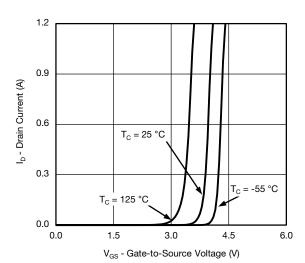
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



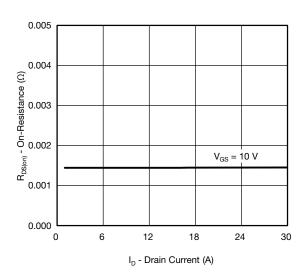
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



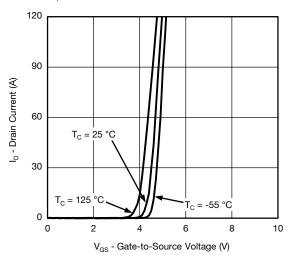
#### **Output Characteristics**



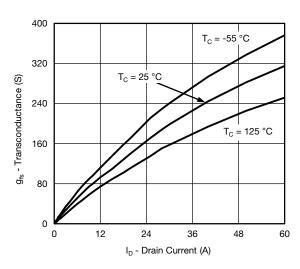
### Transfer Characteristics



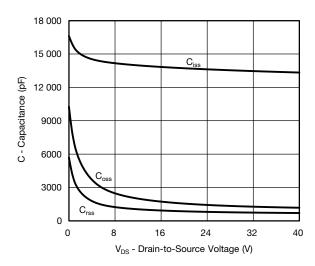
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



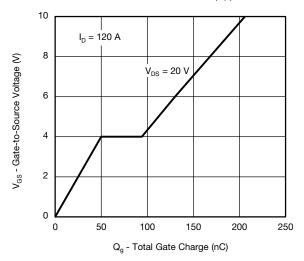
#### Transconductance



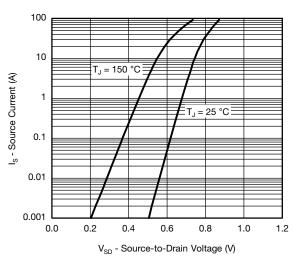
Capacitance



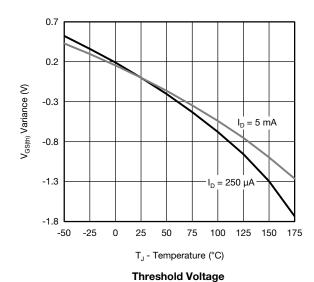
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Gate Charge**



## Source Drain Diode Forward Voltage



0.5

-50

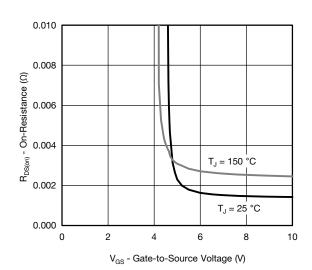
-25

0 25 50

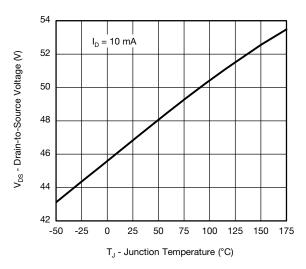
T<sub>J</sub> - Junction Temperature (°C)

100 125

#### On-Resistance vs. Junction Temperature



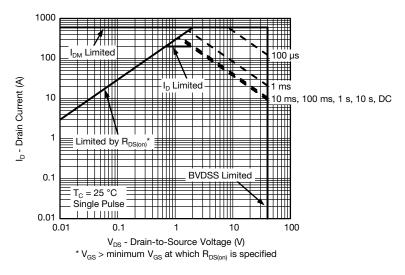
On-Resistance vs. Gate-to-Source Voltage



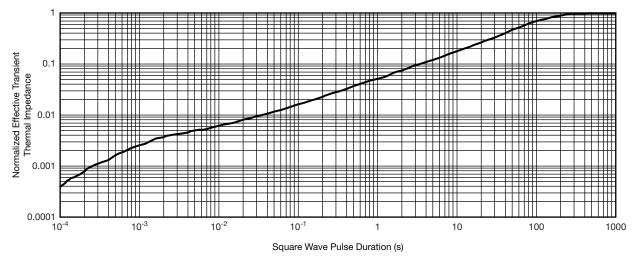
Drain Source Breakdown vs. Junction Temperature



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



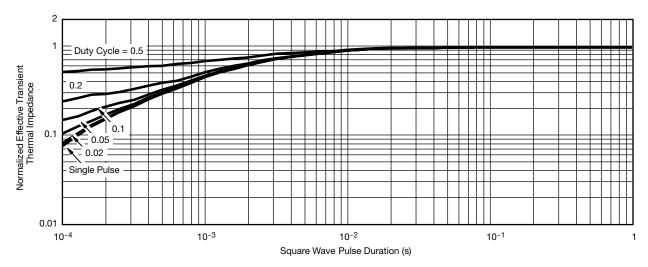
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267184">www.vishay.com/ppg267184</a>.



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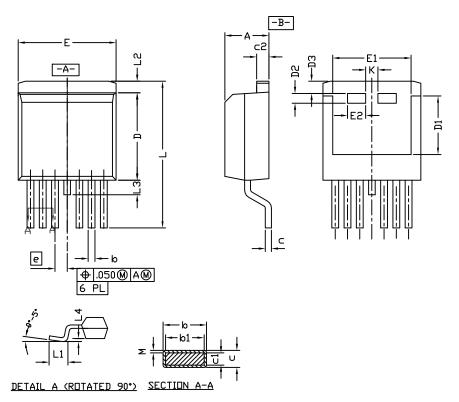
REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
В	04-Aug-15	Revised R <sub>g</sub> minimum limit

#### Note

a. As of April 2014



# D<sup>2</sup>PAK (TO-263-7L) Case Outline



### Notes

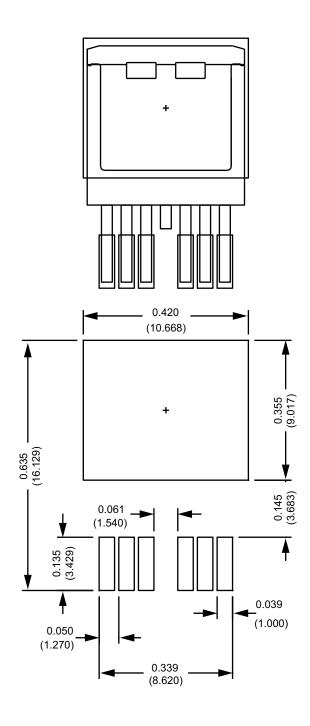
- 1. Plane B includes maximum features of heat sink tab and plastic
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils
- 3. Pin to pin coplanarity max. 4 mils
- 4. Lead thickness 25 mils
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils
- 6. For reference only
- 7. Use inches as the primary measurement
- 8. This feature is only for SUM

	INC	HES	MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.260	0.280	6.604	7.112	
D2	0.046	0.050	1.168	1.270	
D3	0.045	0.055	1.143	1.397	
Е	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050	BSC	1.27	BSC	
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010	BSC	0.254	BSC	
М	-	0.002	-	0.050	
ECN: T17-0433-Rev. C, 14-Aug-17 DWG: 6006					

Revision: 14-Aug-17 1 Document Number: 63782



# Recommended Land Pattern D<sup>2</sup>PAK (TO-263-7L)





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